



NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLV33F** is Designed for Operation in Band III TV Transposers and Transmitter Amplifiers from 170 to 230 MHz.

FEATURES:

- Gold Metalization
- Internal Input Matching
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	$1.5^\circ C/W$

PACKAGE STYLE .500 6L FLG		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.150/3.43	.160/4.06
B	.045/1.14	
C	.210/5.33	.220/5.59
D	.835/21.21	.865/21.97
E	.200/5.08	.210/5.33
F	.490/12.45	.510/12.95
G	.003/0.08	.007/0.18
H	.125/3.18	
I	.720/18.29	.730/18.54
J	.970/24.64	.980/24.89
K	.095/2.41	.105/2.67
L	.150/3.81	.170/4.32
M	.280/7.11	

1 = COLLECTOR 2 = BASE
3 & 4 = EMITTER

ORDER CODE: ASI10493

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA		35			V
BV_{CER}	$I_C = 50$ mA	$R_{BE} = 10 \Omega$	60			V
BV_{EBO}	$I_E = 10$ mA		4.0			V
I_{CES}	$V_E = 28$ V				5	mA
h_{FE}	$V_{CE} = 5.0$ V	$I_C = 1.0$ A	10		100	---
C_{ob}	$V_{CB} = 28$ V	$f = 1.0$ MHz			80	pF
G_{PE}	$V_{CE} = 25$ V	$I_{CQ} = 3.2$ A	13.5	14.5		dB
IMD_3	$P_{REF} = 16$ W	Vision = -8 dB Side Band = -16 dB			-55	dBc